

## EP-R&D Silicon Working Group 1.1

**Hybrid Detectors** 



## Small pitch 3D Timing (& planar <sup>(2)</sup>)

**Evangelos** – Leonidas Gkougkousis

CERN EP-R&D



CERN – June 23<sup>nd</sup>, 2022

# Introduction, EP-R&D W.P. 1.1 – Hybrid Sensors

Planar Sensors (J. Haimberger, V. Gkougkousis)

- ✓ Radiation damage and trapping model validation though TCAD
- ✓ Timing and efficiency at < 1e17  $n_{eq}$ /cm<sup>2</sup> using fast neutrons and ps protons (thicknesses 50, 100, 200, 300 µm)

#### LGADs (V. Gkougkousis)

- ✓ Radiation damage mechanisms and modeling on different dopant types (<u>TIPP2021</u>, <u>ArXiV Preprint</u>, <u>PicoSecond Workshop 2021</u>)
- ✓ Indium-Lithium gain layer radiation hardness investigations (<u>Trento2021</u>)
- ✓ Process simulations and SiMS Carbon/Boron (LINK)

#### Silicon Electron Multiplier (M. Halvorsen, LINK, ArXiV Preprint, IEEE)

- ✓ Structure optimization and electrostatic simulations.
- ✓ Timing and transient Simulations
- ✓ Process iterations (Metal Assisted Etching)

### Small Pitch 3Ds for tacking and timing (V. Gkougkousis, LINK)

- $\checkmark~\beta$  particles timing studies on irradiated and unirradiated devices
- ✓ Test beam with SPS pions (Tracking + Timing)
- ✓ Proton and neutron irradiations > 1e17  $n_{eq}/cm^2$
- $\checkmark$  New small pitch production optimized for gain at electrode region







Victor Coco Paula Cliins

Experiment specific resources (LHCb, Exp @ SPS, other R&D pr 2020 2021 2023 20222024Post-irradiation Characterisation Irrad Thin planar Characterisation 3D LGAD: C co-implant charact. Indium, Lithium co-implantation iLGAD SiEM (simu) SiEM (prod) Simulation (TCAD + signal simulation): radiation damage modeling, input for sensor reoptimisation and IC block design, etc.. Optimisation of system level timing **TPX4** telescope construction M D +sensor upgrade phasel phase2 Fast timing setup integrated to EUDET telescope Submit 28nm analog FE design Test MPW Participation to a 28nm prototype ASIC for R&D Vagelis Gkoukousis MPX4 Fellow 1 Fellow 2 Mohammad Hajheidari Fellow 3 Marius Halvorsen PhD<sub>1</sub>

#### E. L. Gkougkousis

Talks @ Trento 2022

# •3D Sensors

## Timing at Extreme Fluences

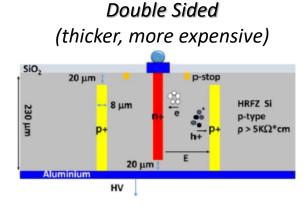
**3D Sensors:** Decoupling of charge generation and drift volume (*Standard columns, TimeSpot, Hex geometries* ect.)

### Pros

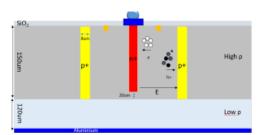
- High radiation tolerance up to several times 10<sup>16</sup> n<sub>eq</sub>/cm<sup>2</sup>
- Short drift distances with fast rise times
- Reduced Landau fluctuation, practically non-existent for perpendicular tracks

#### Cons

- Non-uniform field geometry
- High cost
- Increased cell capacitance



Single Sided (thinner, simpler process)





### Pixel Size vs Field Uniformity

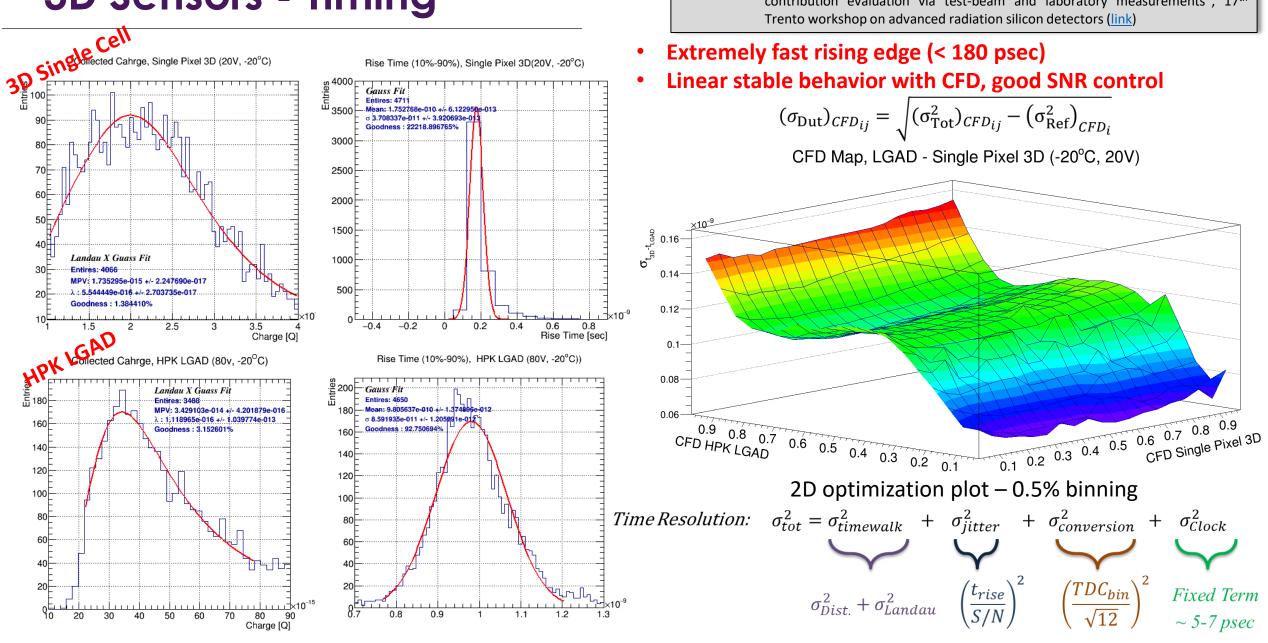
### ATLAS IBL TYPE

- ✓ Double sided n-on-p process
- ✓ Pixel Size 55 × 55  $\mu$ m<sup>2</sup>
- ✓ Active thickness 230 µm
- ✓ High Resistivity (> 2 k $\Omega$ m × cm) Fz silicon

## ATLES Pre-Production type

- ✓ Single sided n-on-p process
- ✓ Pixel Size  $25 \times 100 \ \mu m^2$
- ✓ Active thickness 150 µm
- ✓ High Resistivity (> 2 k $\Omega$ m × cm) Fz silicon
- ✓ Single sided n-on-p process
- ✓ Pixel Size  $50 \times 50 \ \mu m^2$
- ✓ Active thickness 150 µm
- ✓ High Resistivity (> 2 k $\Omega$ m × cm) Fz silicon

# •3D Sensors - Timing



Presentation: V. Gkougkousis, "Single cell 3D timing: Time resolution assessment and Landau

contribution evaluation via test-beam and laboratory measurements", 17th

E. L. Gkougkousis

# Planar Sensors

**Sensors:** CERN EP-R&D n-on-p planar sensor run with ADVACAM at 50, 100, 200 and 300 μm active thickness (TimePix4 bonded sensors also from this run, see Kazu's talk <u>here</u>)

### **Test Structures**

- Small diodes (3.14 mm2 active area) Circular diodes for timing studies due to lower capacitance
- Big diodes (28.27 mm2 active area) Circular diodes for radiation damage studies
- 5x5 Pixel matrix (0.003 mm2 active area) for charge sharing and interpixel efficiency – timing studies

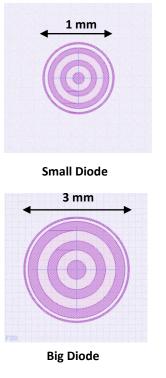
#### Issues

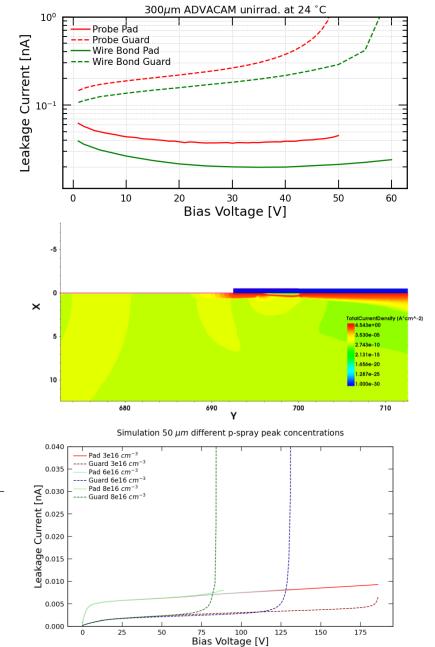
- Early breakdown due to high p-spray concentration leading to impact ionisation at the interface between p-spray and electrode implant
- Breakdown first visible in guard ring due to bigger interface region compared to pad

### Irradíatíons

#### (both 3D and planar)

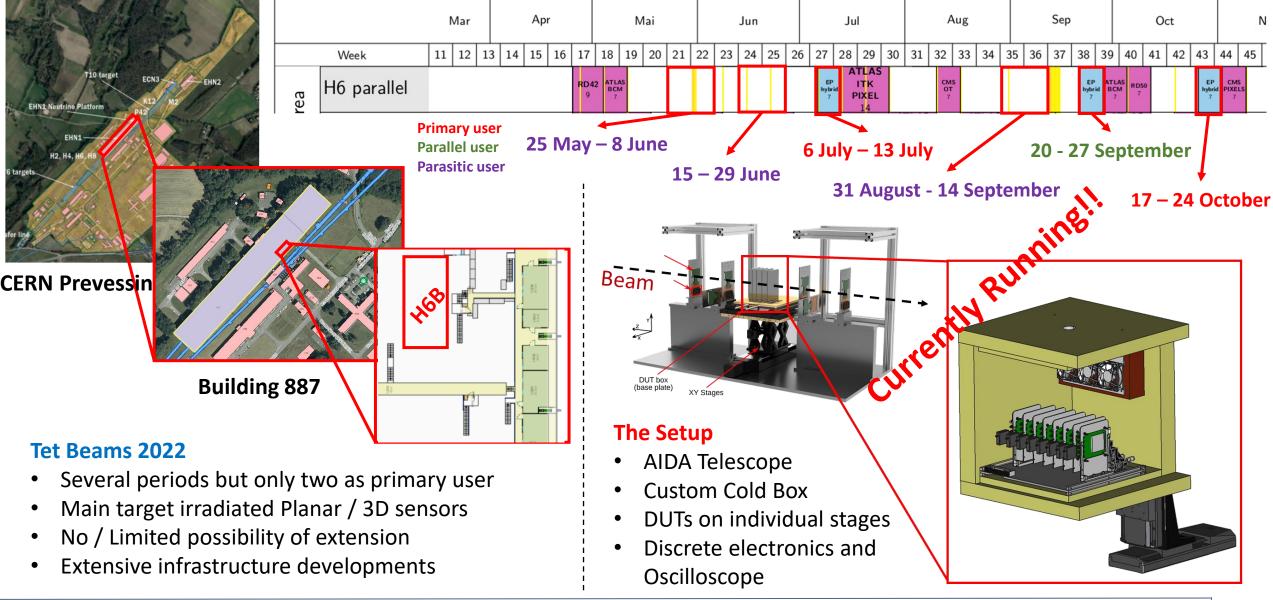
**Neutron** @ JSI (Ljubljana) **Proton** @ PS





# Test Beam Planning





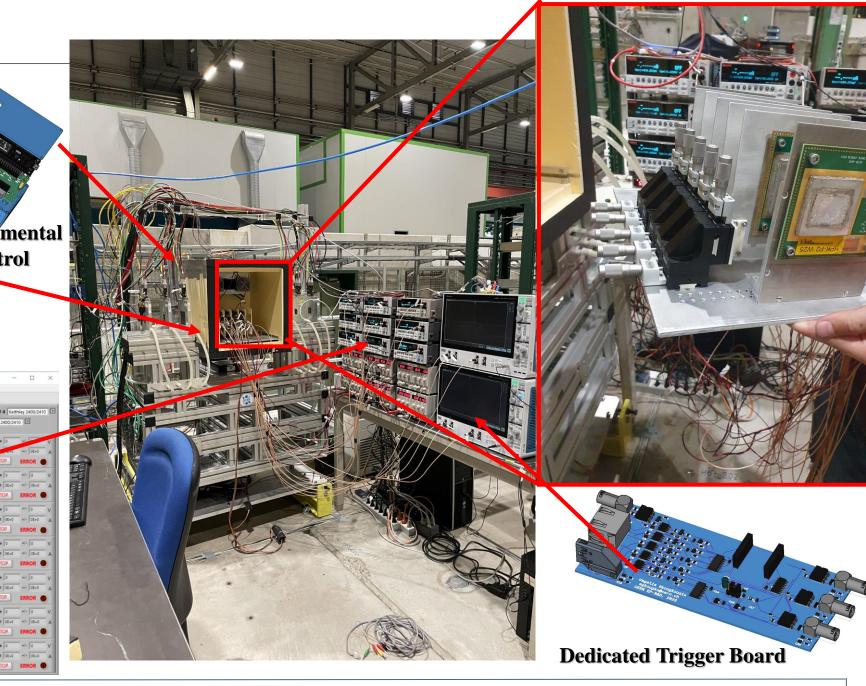


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## Environmental Control

### **XPS Cold Box**

D Timming Setup Configuration		-	D X				
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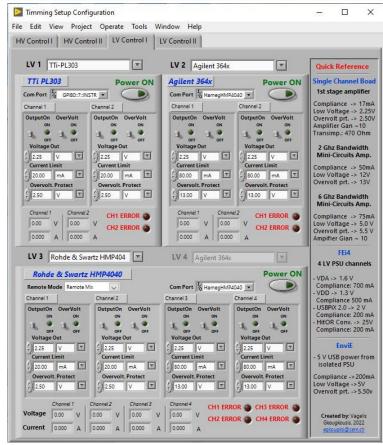
## Test Beam Configuration

**Pixelated plane** LGAD1 CH2A CH3A CH4A LGAD2 CH2B CH3B CH4B FEi4

#### June Test Beam Planning

	_	Sample type	Sample no.	Fluence (n <sub>eq</sub> /cm²)	
=	LGAD Planes	Reference LGADs	2	Unirradiated	
		Single Cell 3D, n-in-p,	1	Unirradiated	
		2-sided, High Res. 285 μm thick	1	$1 \times 10^{15}$	
BEAN	1	55 μm pitch 1 mm² planar diodes	1	8 × 10 <sup>15</sup>	
			$1x50\mu m$ thick	Unirradiated	
		I mm planar diodes	$1x100\mu m$ thick	Unirradiated	
3D singl	e cell sensors		<ul> <li>9 x Kei</li> <li>6 x TTi</li> <li>8 Seco</li> </ul>	cilloscopes thley 2410 PL303 nd stage amplifiers	
			· 100 ·	o-positioning stage ity – Temperature	

## •HV & LV Control/monitoring

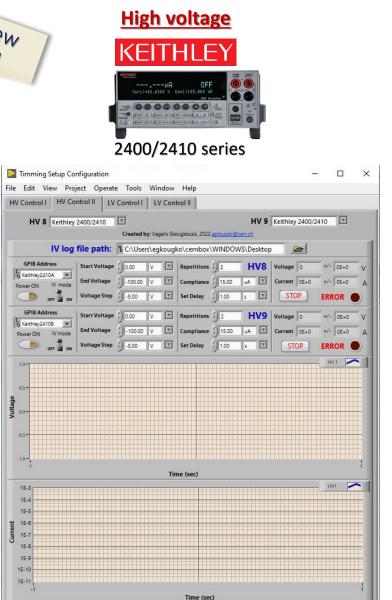


#### **Multi-model Support with Polymorphic UI**

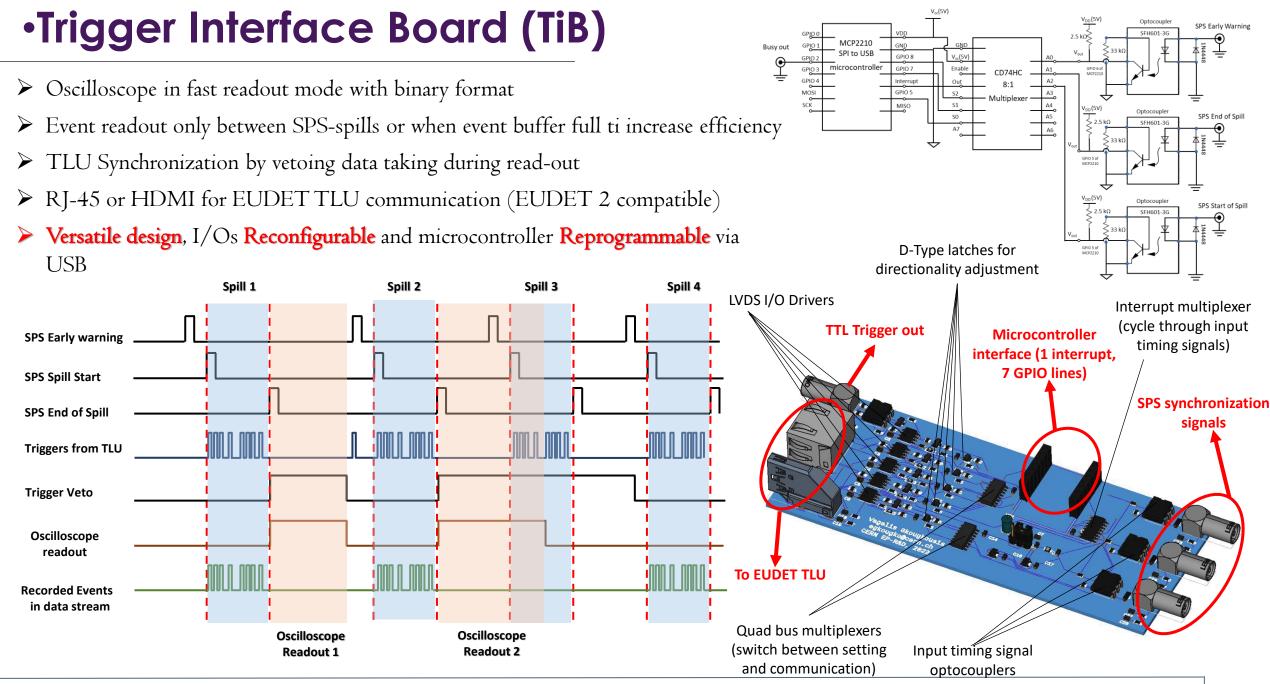


#### Labview Timming Setup Configuration File Edit View Project Operate Tools Window Help based HV Control I HV Control II LV Control I LV Control II HV 1 Keithley 2400/2410 🗹 HV 2 Keithley 2400/2410 🗹 HV 3 Keithley 2400/2410 🖾 HV 4 Keithley 2400 HV 5 Keithley 2400/2410 T HV 6 Keithley 2400/2410 T HV 7 Keithley 2400/2410 T Created by: Vagelis Gkougkousis, 2022 egkougko@cem.c. **GPIB Address** Start Voltage / 0.00 V T Repetitions / 2 HV1 Voltage 0 +/- 0E+0 V Keithley2410A End Voltage / -100.00 V T Compliance / 15.00 UA T Current 0E+0 +/- 0E+0 Power ON IV Mode Voltage Step () -5.00 V V Set Delay () 1.00 s V STOP ERROR GPIR Addres Start Voltage () 0.00 V T Repetitions () 2 HV2 Voltage 0 +/- 0E+0 Keithley24108 End Voltage / -100.00 V T Compliance / 15.00 UA T Current 0E+0 +/- 0E+0 Power ON IV mode 2 OFF ON Voltage Step ()-5.00 V T Set Delay () 1.00 s T STOP ERROR **GPIB Address** Start Voltage () 0.00 V T Repetitions () 2 HV3 Voltage 0 +/- OE+0 Keithley2410A End Voltage ( )-100.00 V T Compliance ( )15.00 UA T Current 0E+0 +/- OE+0 A Power ON IV mode Voltage Step () -5.00 V T Set Delay () 1.00 s T STOP ERROR **GPIB Address** Start Voltage () 0.00 V T Repetitions () 2 HV4 Voltage 0 +/- 0E+0 Keithley24108 End Voltage (+) -100.00 V T Compliance (+) 15.00 uA T Current 0E+0 +/- 0E+0 / Power ON IV mode 4 OFF ON Voltage Step 4-5.00 V T Set Delay 4 1.00 s T STOP ERROR **GPIB Address** Start Voltage 1 0.00 V T Repetitions 1 2 HV5 Voltage 0 +/- 0E+0 V Keithley2410A End Voltage ( - - 100.00 V T Compliance ( 15.00 UA T Current 0E+0 +/- 0E+0 A Power ON IV mode Voltage Step () -5.00 V T Set Delay () 1.00 s T STOP ERROR **GPIB** Addres Start Voltage () 0.00 V T Repetitions () 2 HV6 Voltage 0 +/- 0E+0 V Keithley2410B Power ON IV mode 6 End Voltage 2 .100.00 V T Compliance 2 15.00 uA T Current 0E+0 +/- 0E+0 OFF ON Voltage Step ()-5.00 V T Set Delay () 1.00 5 T STOP ERROR **GPIB** Addres Start Voltage (0.00 V Repetitions 4) 2 HV7 Voltage 0 +/- 0E+0 V Keithley2410B End Voltage / -100.00 V T Compliance / 15.00 uA T Current 0E+0 +/- 0E+0 Power ON IV mode OF ON Voltage Step 0.5.00 V T Set Delay 0.00 s STOP ERROR 9x HV channels 16x LV channels Constant monitoring & logging Live protection

### Precompiled executable available on GitLab: <u>here</u>



23 / 6 / 2022



E. L. Gkougkousis

# Temperature Regulation

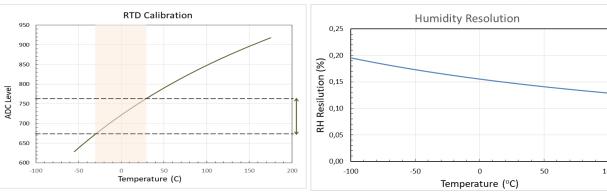
Running at a crisp -18 °C

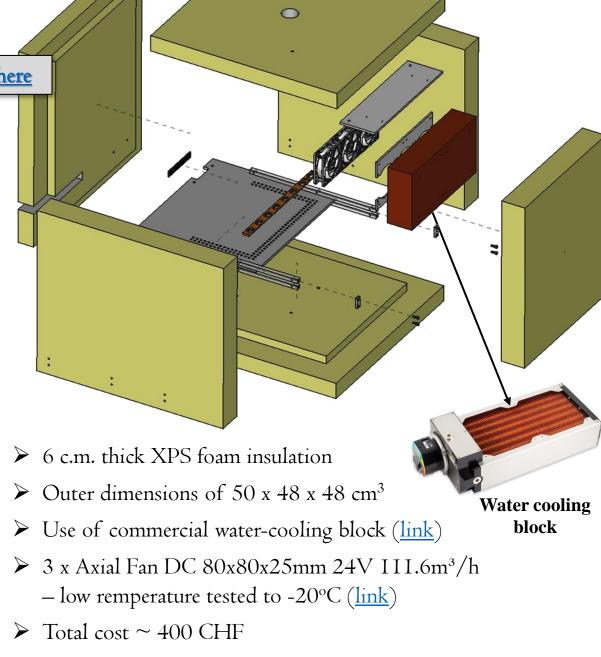
> EnviE GitLab with schematics: <u>here</u>

- ➢ Glycol cooling with temperature feedback Labview control
- $\succ$  Humidity regulation though N<sub>2</sub> feeds

### Environmental Expander V2.0 (EnviE)

- ESP8266 based with integrated 10-bit ADC, I2C and WiFi 802.11b
- Integrated OLED 128X64 pixel screen
- High precision voltage dividers and sensor decoupling
- ARDUINO / LoUA core web interface
- Temperature resolution of 0.8 °C  $\pm$  0.06 %
- Humidity resolution 0.1 % with temperature compensation



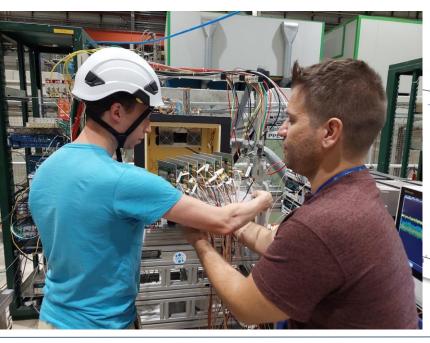


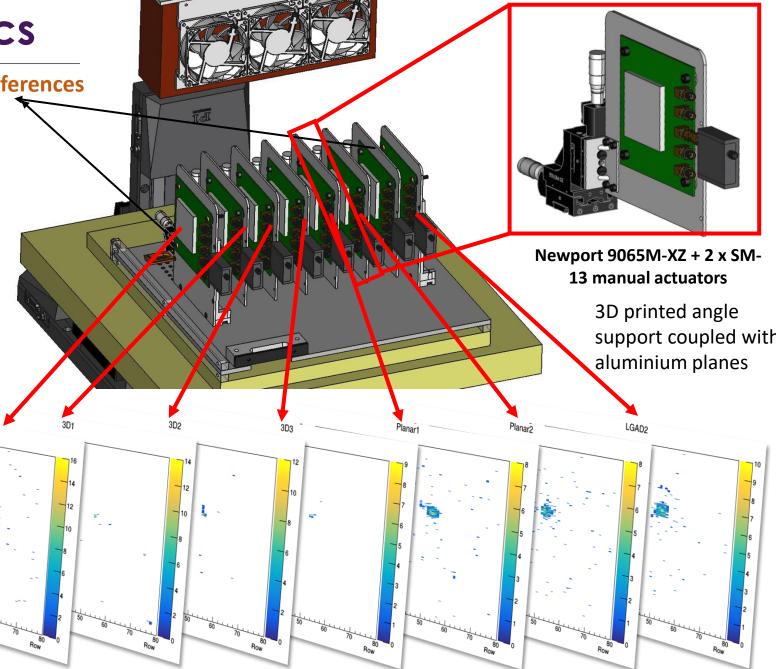
# Alignment & Mechanics

#### HPK LGAD Timing references

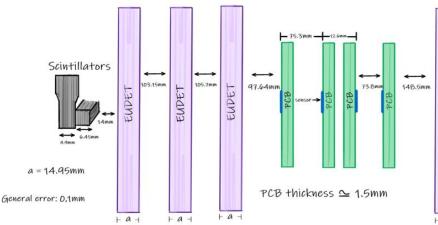
LGAD1

- Coincidences between DUTs and LGADs required for timing
- > Alignment crucial to increase data efficiency
- Efficiency defined by largest overlapping region
- Micrometric on-line alignment using projections on FEi4 matrix
- ROI defined in addition to other trigger conditions



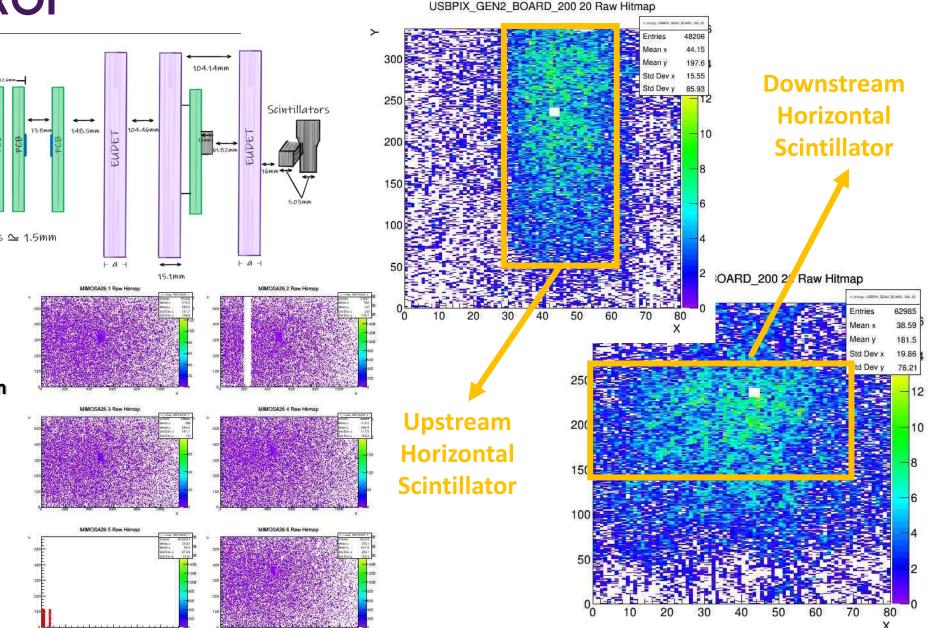




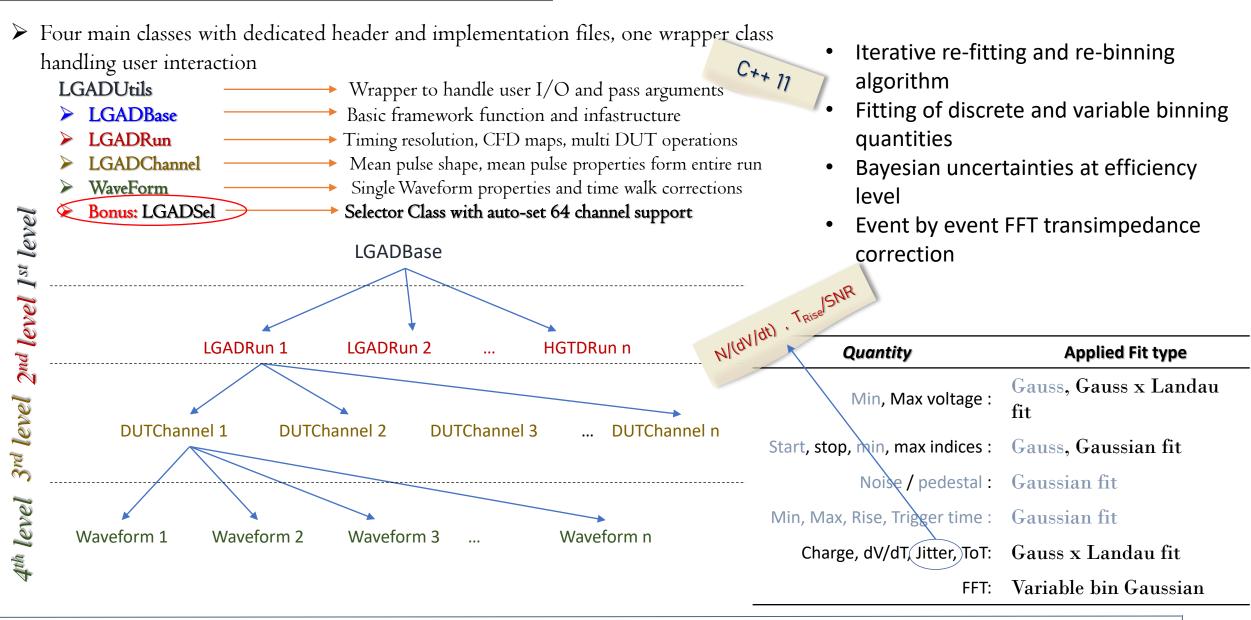


#### **Telescope Planes**

- 6 MIMOSA planes for tracking
- Plane no. 5 known to be bad
- Expected 5µm tracking resolution
- Estimated acquired number of events ~1M
- Limited beam control as parasitic user
- Suffer from low intensity and low data rates of EUDAQ

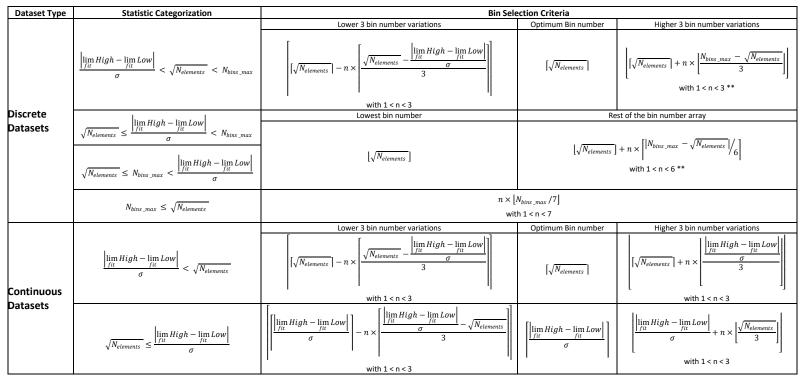


# Analysis Framework



# Iterative Re-fitter & signal templates

- Centralized fitter engine for all fits
- ➢ Fully automated, including limits, method and Minuit minimization
- ➢ 36 Iterations per fit with limits and bin size variation to determine best combination
- Vover-binning protection, automatic variable discreetness test
- Variable binning for FFT, frequency histograms
- Supported ROOFit, Standalone Minuit, Integral optimization or Shape



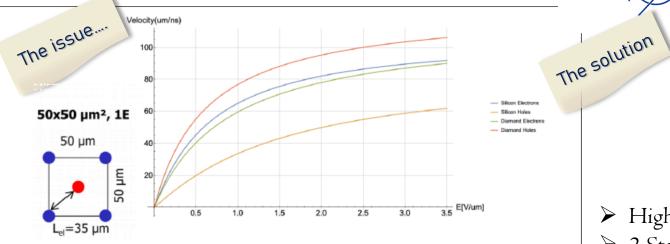
### Template Method

Point by Point projection of all timewalk corrected (though CFD) signal pulses

File: LGADFits.cxx

- Landau X Gauss fit on projected point by point distribution
- Extraction of a "characteristic" signal composed of the MPVs of the Point by point projection fits
- RooKeyPdf for analytical description of signal
- Re-iteration on all events and fit of each waveform with the extrapolated analytical signal description
- Re-caclculate all quantities

# •16 Channel Board



- Assuming a linear filed dependence and a -15 V operation point at 35  $\mu$ m column distance:  $|E| \cong 0.43 V/\mu m$
- Estimating drift velocity for electrons:

$$v_{drift}^{e} = \frac{\mu_{0,e} \times E}{\left[1 + \left(\frac{\mu_{0,e} \times E}{v_{sat.}^{e}}\right)^{\beta_{e}}\right]^{1/\beta_{e}}}$$
  
with  $v_{sat.}^{e} = 107 \ \mu m/ns$ ,  $\mu_{0,e} = 1417 \frac{cm^{2}}{v_{s}}$ ,  $\beta_{e} = 1.109$ 

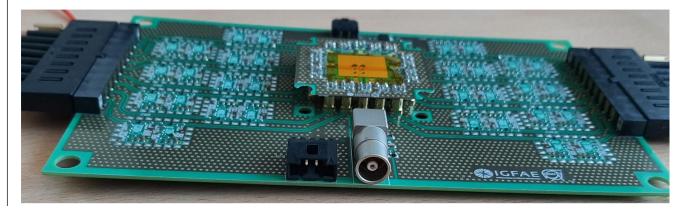
### $v_{drift}^e \approx 41.4 \, \mu m/ns$

• Extrapolated Rise time and Frequency:

$$t_{Rise} \approx \frac{1}{3} \times t_s = \frac{1}{3} \times \frac{d/2}{v_{drift}^e} \approx 140 \ psec \Rightarrow 2.3 \ \text{GHz}$$

July 2021 October 2021 March 2022 August 2022 Timeline
Design submission Initial tests 2<sup>nd</sup> Mezzanine Test beam measurement iteration with planar matrix

- $\clubsuit$  High frequency multichannel versatile board
- \* Mezzanine design for fast sensor interchangeability
- Suitable for matrices (AC-LGAD applications) but also for single pad devices
- ➢ High Frequency SiGe discreate electronics @ 12 GHz bandwidth
- $\blacktriangleright$  2 Stage configuration with a transimpedance followed by a voltage stage
- → Low max current (~10mA) with well behaved gain linearity vs  $V_{DD}$
- Ruggers 3000 High Frequency substrate
- Pre-assembled miniaturized coaxial edge connectors with panelmounted SMA plugs (Im cable length)
- $\blacktriangleright$  140 x140 mm outer dimensions

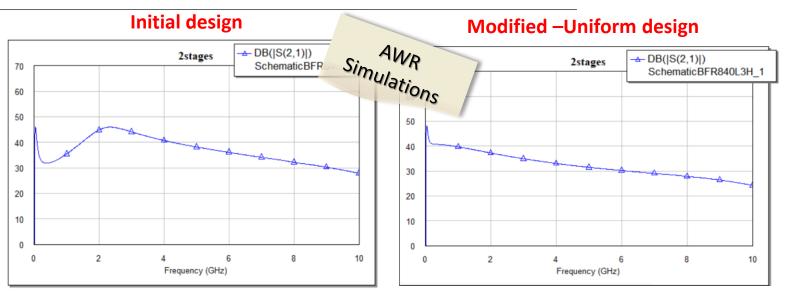


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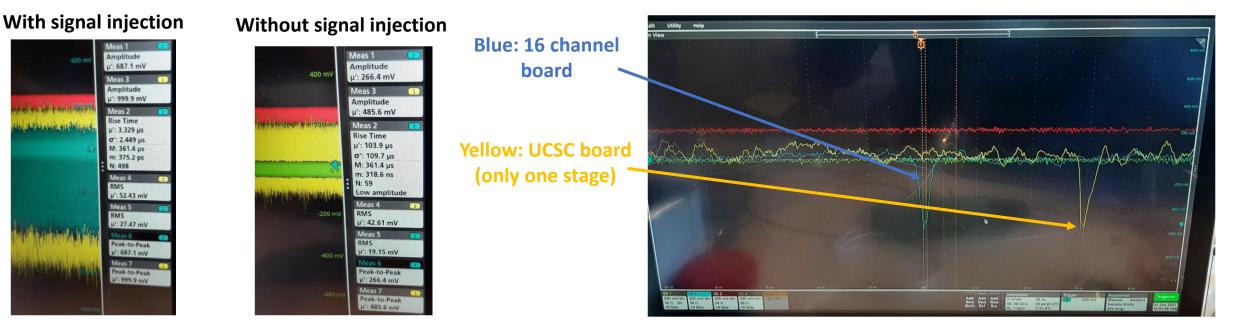
#### E. L. Gkougkousis

GFAE

# Simulations and performance



- Optimized design for uniform response with frequency
- No sharp gain change discontinuities
- No undershoot/overshoot observed
- ➢ Gain moderated to ∼70 for a two-stage configuration
- 20% Higher SNR than UCSC board (with both stages)
- 2 x SNR with respect to UCSC board + niniCircuits second stage amplifier
- On going energy and transimpedance simulation



#### 23 / 6 / 2022

# Towards the Future: Sampic

### The ASIC (SAMPIC)

- Technology: AMS 0.18µm
- Sampling: between 3 and 8.4 GS/sec on 16 channels (depends on DAC setting)
- 16 channels per chip
- Signal Bandwidth of 1.6GHz
- Discrimination noise 2 mV, chip noise < 1.3 mV RMS
- Max input Signal: 1V unipolar (0.1V to 1.1V)

### **ADC**

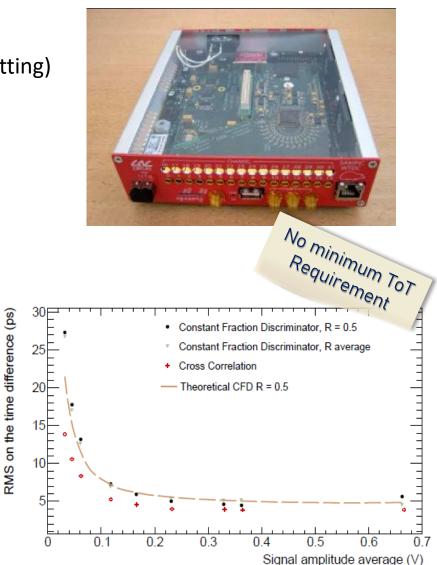
- 8 to 11 bit Wilkinson ADC at 1.3GHz
- Upon triggering 64 samples digitalized in parallel per channel
- Resolution adjustment possible to improve timing by reducing bit count
- Time resolution between 5 ps (calibrated) and 15ps (uncalibrated)

### Calibration

- Calibration files provided for all operational points of the ADC
- Channel by channel calibration to be performed by user
- 64 channels x 4 operation points = 256 calibration runs

### Connectivity

- USB2.0 + LabWindows based software (provided)
- UDP Based Ethernet, direct PC connection no router support



## Conclusions

## 3D Pixels - Planar measurement campaign

- Several productions under investigation of different pixel size and thickness
- Estimate filed non-uniformity impact on time resolution vs pixel size
- Determine minimal acceptable thickness for time resolution applications (SNR)
- Investigate effects after irradiation up to 1e17 n<sub>eq</sub>/cm<sup>2</sup> in protons and neutrons

## **Test-Beam Setup**

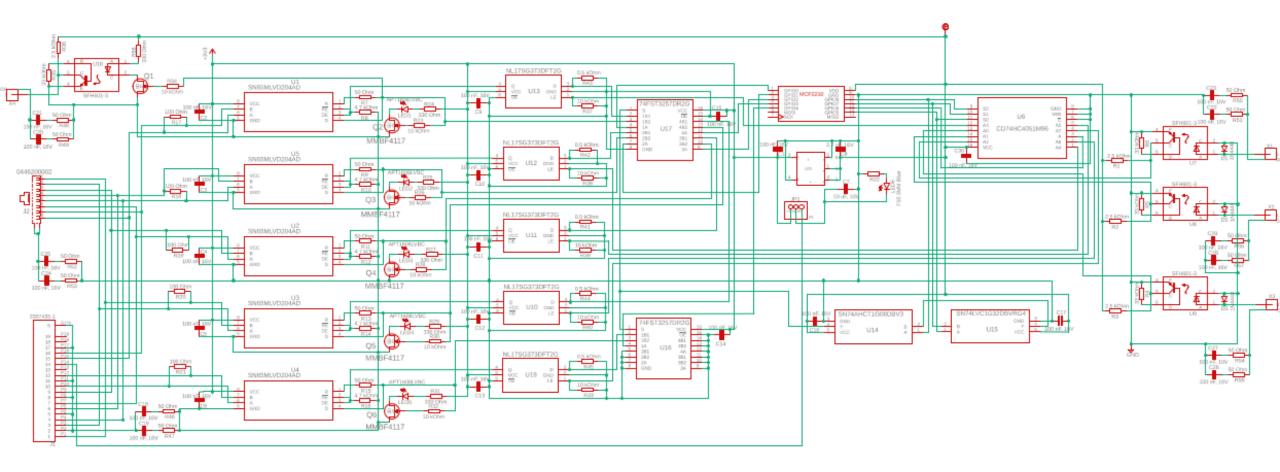
- **Trigger Interface board:** Versatile, allows interfacing any acquisition instrument with EUDET
- Control Software: Polymorphic UI with seemingless multi-instrument support
- Cooling: XPS cold box with web interface temperature controllable system @ -18°C
- Mechanics: Micrometric alignment with individual DUT stages
- **Analysis Framework:** Advanced framework with signal shapes, iterative re-fitting and shape-based noise rejection

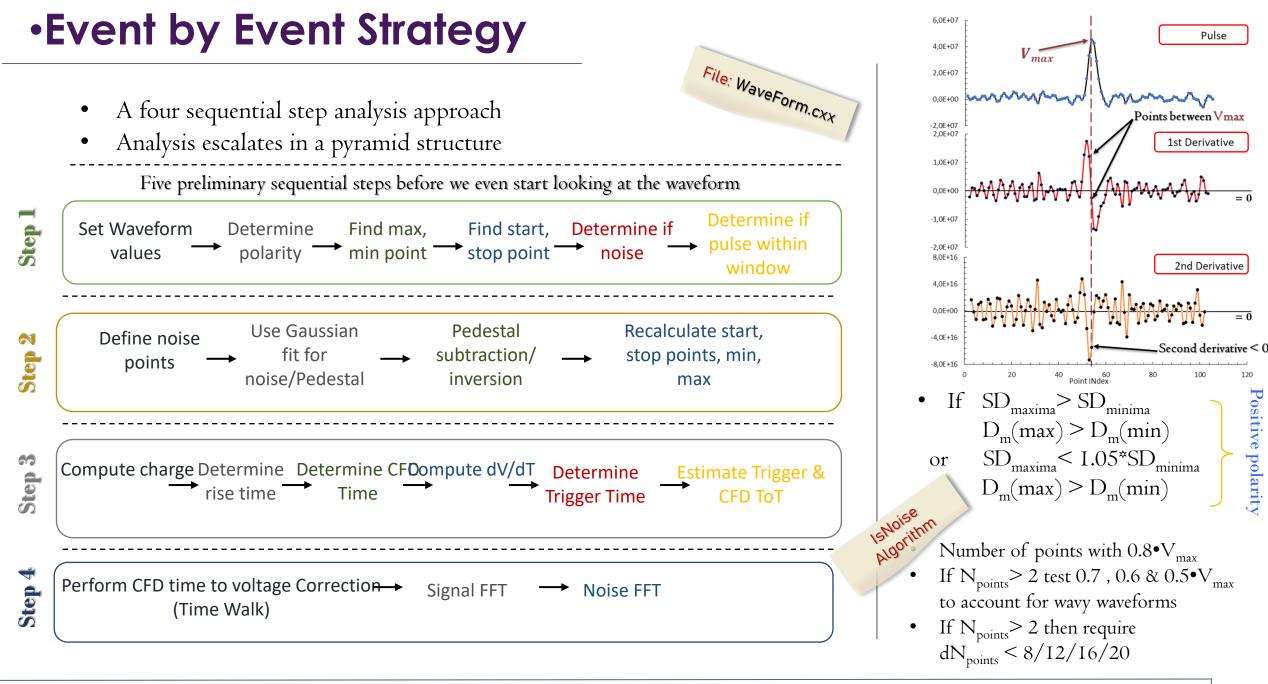
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**Primary Goals** 

# Backup

## TIB Schematics





### •Fits infrastructure

### Available fitting options

Root multi-iterative automatic fitting for:

I. Gauss

#### II. Gauss X Landau



int IterativeFit (std::vector<double> \*w, std::pair<double, double> &gmean, std::pair<double, double> &gsigma, TH1D\* &FitHist, double &minchi2, std::string methode = "Gauss", std::pair<int, int> points = std::make\_pair(-1, -1))

Unpinned 2-dimentional Linear fitting through RooFit and Minuit:

Roofit Convolution fitting (no iterative readjustment) for:

I. Gauss X Landau II. Gauss X Linear

int RooConvFit (std::vector<double>\* vec, std::pair<double, double> &magMPV, std::pair<double, double>
 &magSigma, std::string conv);

> Tow point linear interpolation:

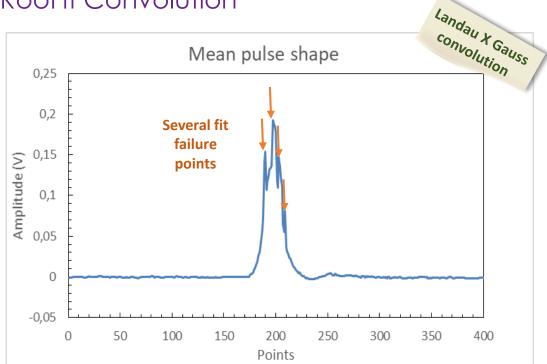
double LinearInter(double x1, double y1, double x2, double y2, double y3);

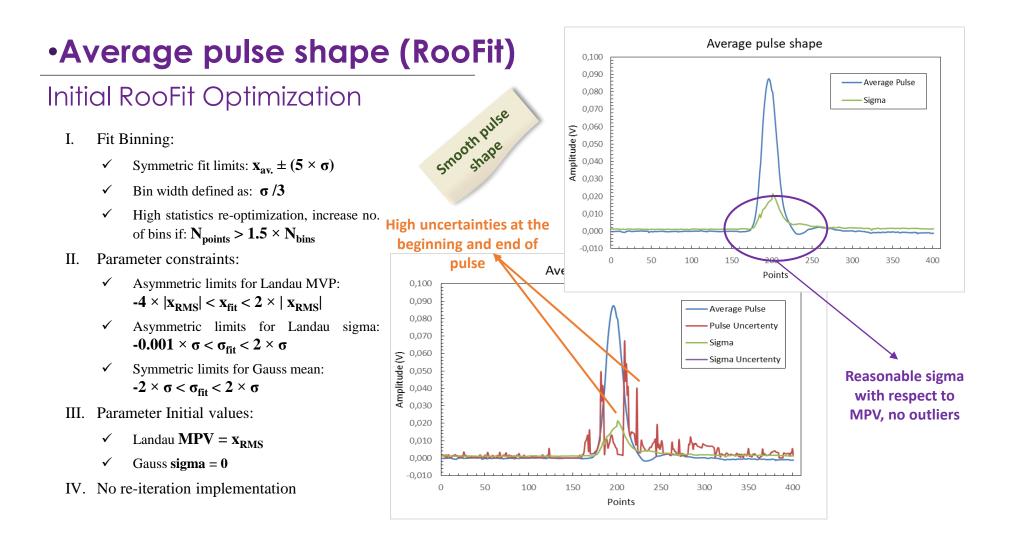
Fast Furrier transform algorithm: double FFT(std::vector<double> \*w, Long64\_t snrate, int start, int stop);

## Average pulse shape (RooFit)

### Starting point, Non-optimized RooFit Convolution

- I. Average calculated from 100 events
- II. Each waveform is time aligned at 20% CFD
- III. For all events, the same point of each waveform projected in TH1F
  - ✓ as many THIF as points in waveform
  - ✓ each with as many entries as events (100 here)
- IV. Each TH1F fitted with a Landau X Gauss distribution
- V. MPV, sigma and uncertainty extracted
- VI. Fitting performed in RooFit using RooFit Convolution and Minuit
- VII. No starting parameters or optimization
- VIII.Plot the MPVs of each point in a single waveform

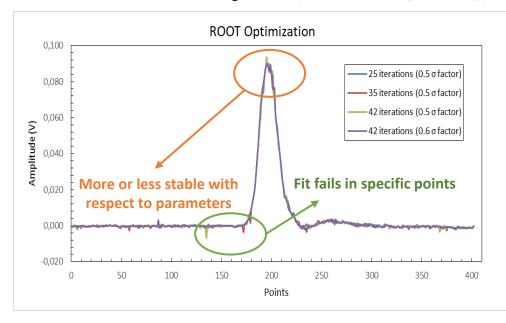


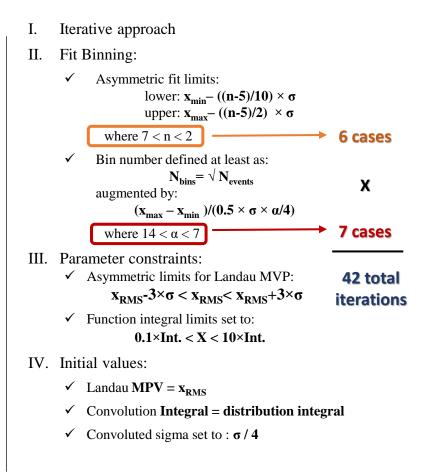


## Average pulse shape (Root)

### Root Optimization (no RooFit)

- Constraint parameter values but not fixed
- Manually defined convolution function
- 1000 convolution steps
- Select the fit with the best agreement (minimization of  $|1-x^2/NDF|$ )





## •LGAD Time Reference

